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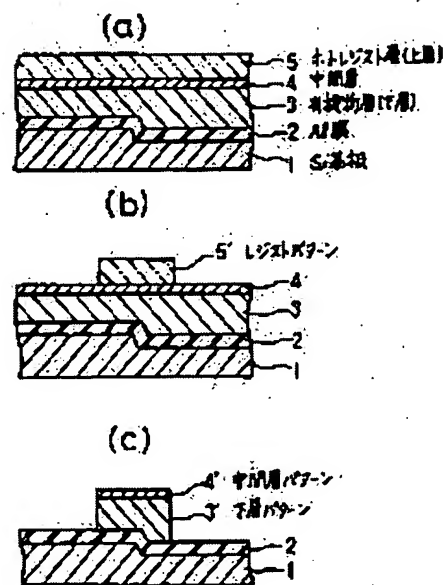
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(54) METHOD OF FORMING PATTERN

(57)Abstract:

PURPOSE: To form an ultrafine pattern by containing aromatic bisazide in a lower organic layer, and reducing a light transmission rate used for the exposure of forming a pattern by heating or exposing the full surface.

CONSTITUTION: An aluminum film 2 of a film to be formed is formed on an Si substrate 1 having a step on the surface. An organic layer 3 of the lower layer for flattening the step is formed by using as a polymer polyvinylphenol, as aromatic azide compound 1-(p-azidebenzylidene)-3-(α -hydroxybenzyl)indene(bisazide I) of 20wt% to the polymer, dissolving in a cyclohexane of a solvent, and spin coating it. Then, a silicon compound and positive type photoresist are coated as an intermediate layer 4, a photoresist phase 5 is formed, and the desired resist pattern 5' is formed by a normal photolithographic method. Then, with the pattern 5' as a mask the layer 4 is selectively etched to obtain patterns 3', 4' of accurate dimension and preferable shape.



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